

# ECN3067

ECN3067 is monolithic IC integrating 6 IGBTs.

It can be applied to DC brushless motors and Induction motors.

## Functions

- Free Wheeling Diodes are integrated
- Overcurrent Protection Circuit is integrated
- Undervoltage Detection Circuit is integrated

## Features

- PWM control of upper and bottom arm IGBTs are possible with an outer Microprocessor.
- 6 Logic inputs are compatible with 5V CMOS or LSTTL outputs.
- Upper and Bottom arm IGBTs can operate in 20kHz chopping frequency.
- For converted AC200 to 230 V power supplies PWM control of top and bottom arm IGBTs are possible.

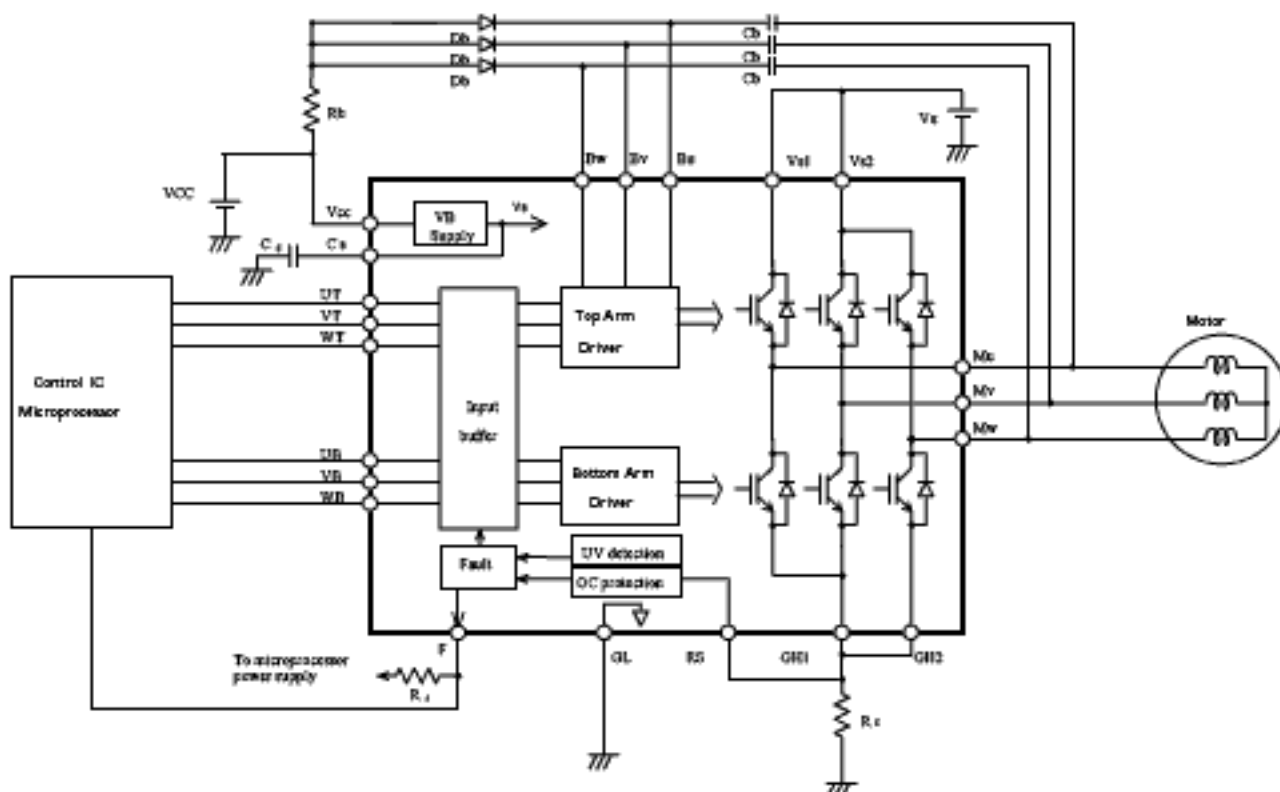


Fig.1 Block Diagram(example for boot strap)

# ECN3067

## 1. General

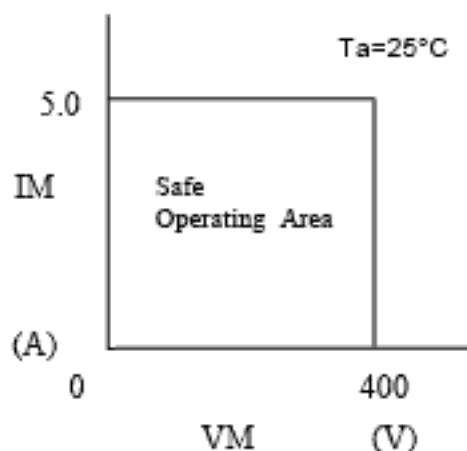
- (1) Type : ECN3067SLV, ECN3067SLR  
 (2) Application : 3-Phase DC Brushless Motors and Induction Motors  
 (3) Structure : Monolithic IC  
 (4) Package : SP-23TE, SP-23TFA

## 2. Absolute Maximum Allowable Ratings (Ta=25°C)

No.	Items	Symbols	Terminal	Ratings	Unit	Condition
1	Output Device Breakdown Voltage	VSM	VS1,VS2 MU,MV,MW	500	V	
2	Supply Voltage	VCC	VCC	18	V	
3	Input Voltage	VIN	UT,VT,WT, UB,VB,WB	-0.5~VB+0.5	V	
4	Output Current	IOM	MU,MV,MW	5.0	A	Note 1
5	Operating Junction Temperature	Tjop		-20~+135	°C	Note 2
6	Storage Temperature	Tstg		-40~+150	°C	

### Note 1. Recommended Safety Operation Area

It is recommended that this IC is used within the SOA as shown below where IM and VM are the current and the voltage at the terminal of motor wiring at the change of phase (turn on and turn off).



### Note 2. Thermal Resistance

$$R_{jc} = 1.5^{\circ}\text{C/W}$$

## 3. Recommended Operating Conditions

No.	Items	Symbols	Terminal	MIN.	TYP.	MAX.	Unit	Condition
1	Supply Voltage	VS	VS1,VS2	50	—	400	V	
2		VCC	VCC	13.5	15	18.5	V	
3	Supply Current	IS	VS1,VS2	—	—	2.5	A	

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## 4. Electrical Characteristics

Unless otherwise specified,  $V_{CC}=15V$ ,  $V_S=325V$

Suffix T: Top arm B: Bottom Arm

$T_a = 25^\circ C$

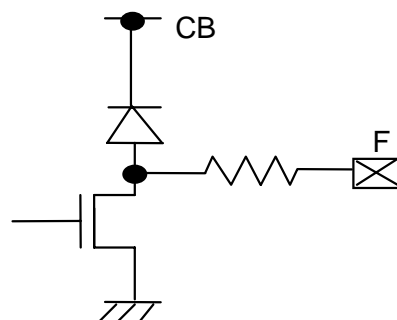
No.	Items		Symbols	Terminal	MIN.	TYP.	MAX.	Unit	Condition
1	Standby Current		IS	VS1,VS2	—	—	0.25	mA	Input=“H”
2			ISB	BU-MU,BV-MV,BW-MW	—	15	30	μA	BU-MU,BV-MV, BW-MW=15V
3			ICC	VCC	—	10	20	mA	
4	Output device FVD		VFT	MU,MV,MW	—	2.5	3.5	V	I=1.5A PW<5ms
5			VFB	MU,MV,MW	—	2.5	3.5	V	I=1.5A PW<5ms
6	Turn On Delay Time		TdONT	MU,MV,MW	—	1.0	2.0	μs	I=1.5A Resistive Load
7			TdONB	MU,MV,MW	—	1.0	2.0	μs	
8	Turn Off Delay Time		TdOFFT	MU,MV,MW	—	1.0	2.0	μs	
9			TdOFFB	MU,MV,MW	—	1.0	2.0	μs	
10	Diode FVD		VFDT	MU,MV,MW	—	2.5	3.5	V	I=1.5A
11			VFDB	MU,MV,MW	—	2.5	3.5	V	PW<5ms
12	Input Voltage		VIH	UT,VT,WT,	3.5	—	—	V	
13			VIL	UB,VB,WB	—	—	1.5	V	
14	Input Current		IIL	UT,VT,WT, UB,VB,WB	-100	—	—	μA	Input=0V Note 1
15			IIH		-30	—	—	μA	Input=5V Note 1
16	VB Output Voltage		VB	CB	6.8	7.5	8.2	V	
17	VB Output Current		IB	CB	50	—	—	mA	δVLOAD= 0.2V
18	Over Current reference Voltage		Vref	RS	0.45	0.5	0.55	V	
19	Fault output on resistance		Ronf	F	—	300	400	Ω	Note 2
20	Vcc Under Voltage	Negative Going	Vuvb	VCC	9.8	11.4	13.0	V	Note 3
21		Reset Hysteresis	Vrhb	VCC	0.1	0.4	0.9	V	
22	VBU,BV,BW Under Voltage	Negative Going	Vuvt	BU-MU,BV-	9.8	11.4	13.0	V	Note 4
23		Reset Hysteresis	Vrht	MV,BW-MW	0.1	0.4	0.9	V	
24	Fault reset delay time		tflrs	F	6.5	10	20	μs	
25	OC shutdown delay		toc	RS	—	2.0	3.0	μs	

Note 1. Pull Up Resistance are typically 200k $\Omega$

Note 2. The equivalent circuit around F terminal is shown below.

Note 3. Please see item 5.4.

Note 4. Please see item 5.4.



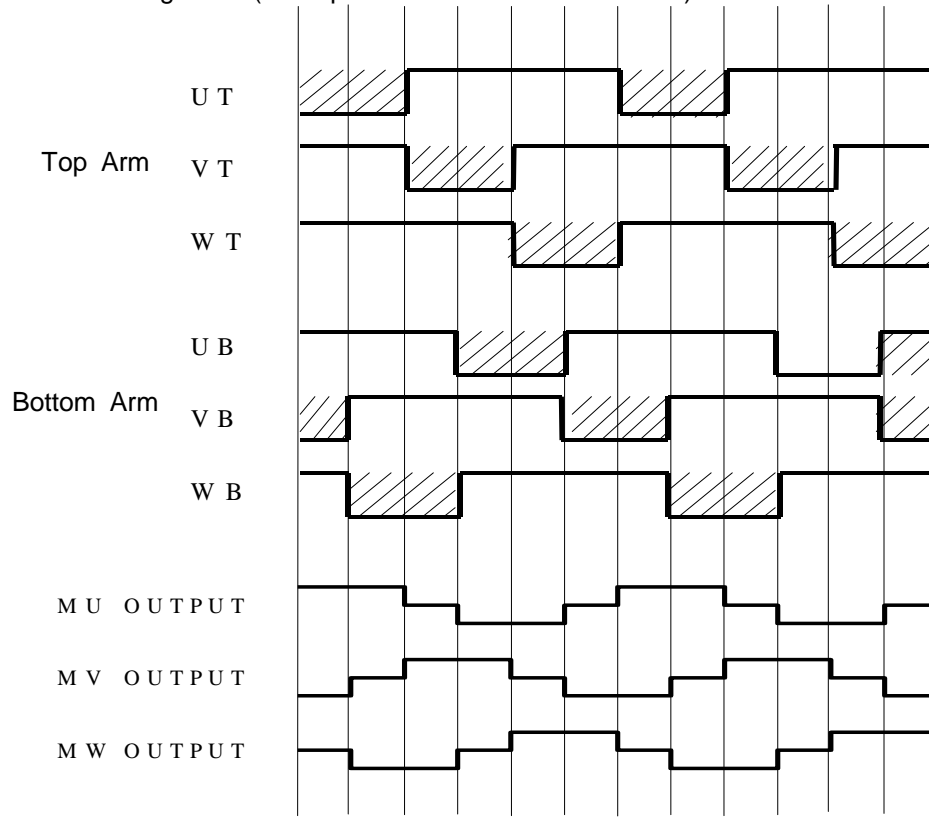
# ECN3067

## 5. Function

### 5.1. Truth Table

Terminal	Input	Output
UT,VT,WT, UB,VB,WB	L	ON
	H	OFF
UT,UB	UT&UB=L	OFF
VT,VB	VT&VB=L	OFF
WT,WB	WT&WB=L	OFF

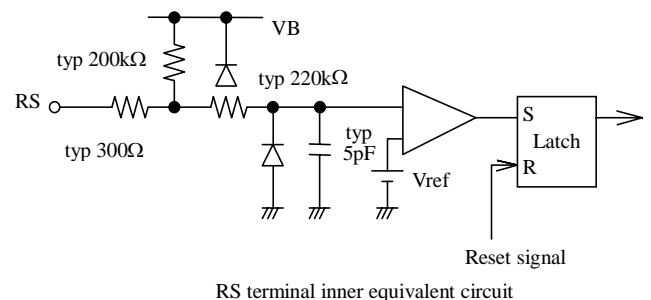
### 5.2 Timing Chart(Example of Brushless Motor drive)



### 5.3 Over Current Operation

This IC detects over current by checking the Voltage drop at the external resistance RS. When the input voltage at RS terminal exceeds the internal reference voltage (Vref), this IC turns off the output of all arms circuit and F terminal output becomes "L". After over current detection, reset is done when all six inputs are referenced to high level.

In case of not using this function, please connect this terminal to GL terminal (within 100 Ω).

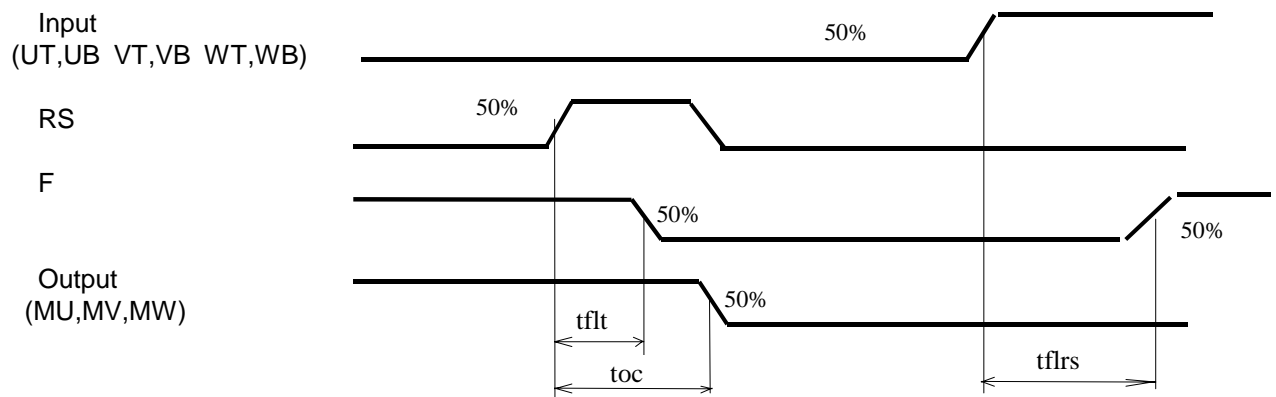
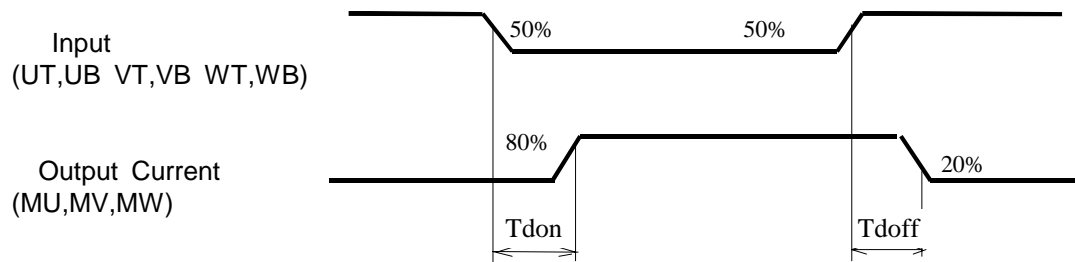


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## 5.4 Undervoltage Detection

- 1) When  $V_{cc}$  supply voltage becomes below  $V_{uvb}$ (11.4V typ.), all of the IGBTs shut off and F terminal output becomes "L".
  - 2) When between BU-MU, BV-MV or BW-MW voltage become below  $V_{uvt}$ (11.4V typ.), top arm IGBT of under voltage detected phase shuts off. In this time, F terminal output doesn't change.
- Note 1. When  $V_{CC}$  supply voltage becomes lower, driving capability of IGBT also becomes lower. Accordingly, power dissipation becomes higher and this causes temperature raise of IC. In case of junction temperature exceeds 135°C, IC may deteriorate or breakdown.

## 5.5 Definition of switching delay



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## 6.Standard Application

No	ITEMS	SYMBOLS	UNIT	VALUESTOL.	REMARK
1	VB Smoothing Capacitor	Co	μF	≥ 0.22	Stress Voltage 8V
2	Boot Strap Capacitor	Cb	μF	≥ 3.3	Stress Voltage Vcc
3	Boot Strap Diode	Db	–	Hitachi DFG1C6, DFM1F6 or equivalent	Breakdown Voltage : ≥ 600V, Current : ≥1.0A Trr : ≤ 200ns
4	Sensing Resistor	Rs	Ω	Note1	
5	Load resistor for F terminal	Rf	kΩ	≥ 5.6	
6	Resistor of boot strap	Rb	Ω	Note2	

Note1. Over-current detection level is determined by the following equation.

$$I_o = V_{ref} / R_s \quad (A)$$

Note2. Current limiting resistance Rb is prevention over current protection from operation at initial charge. Rb is about determined by the following equation.

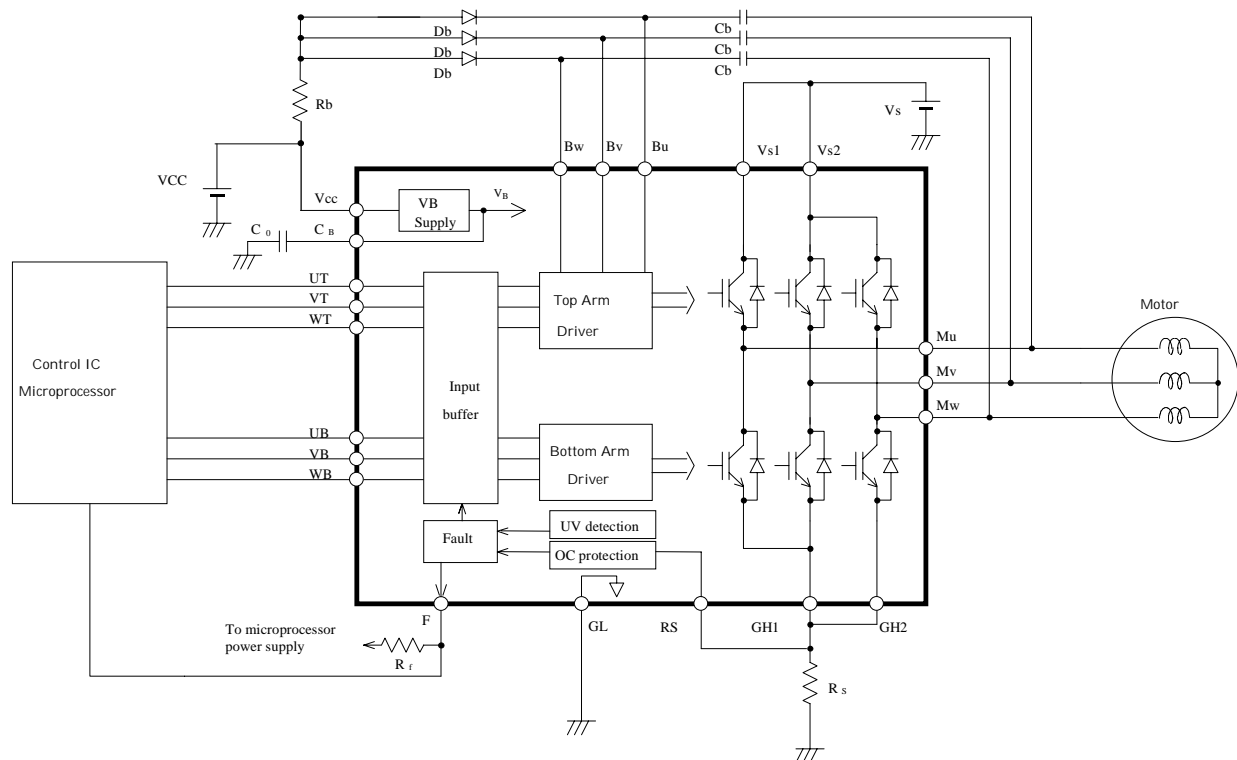
$$I_{bpeak} = V_{ref} / R_s = V_{CC} / R_b$$

$$R_b > (V_{CC} * R_s) / V_{ref} * 2$$

( \* 2 shows the margin. Top arms are off state. Ibpeak is one phase only.)

Ibpeak : Peak current of the initial charge for Cb

Vref ; Over Current reference Voltage



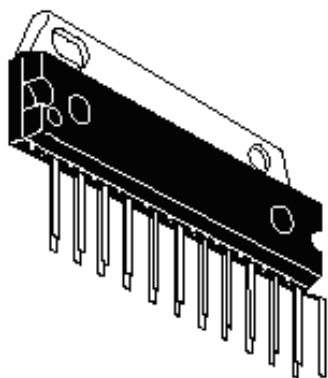
Block Diagram(example for boot strap)

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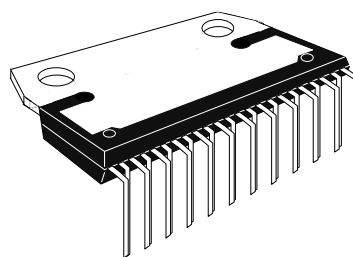
## 7. Pin Assignment

Pin No.	Terminal Name	Pin No.	Terminal Name
1	MV	13	VB
2	VS2	14	UB
3	MW	15	WT
4	GH2	16	VT
5	BW	17	UT
6	BV	18	BU
7	VCC	19	VS1
8	CB	20	Non Connection
9	GL	21	Non Connection
10	F	22	MU
11	RS	23	GH1
12	WB		

## 8. Package Outline



ECN3067SLV  
(SP-23TE)

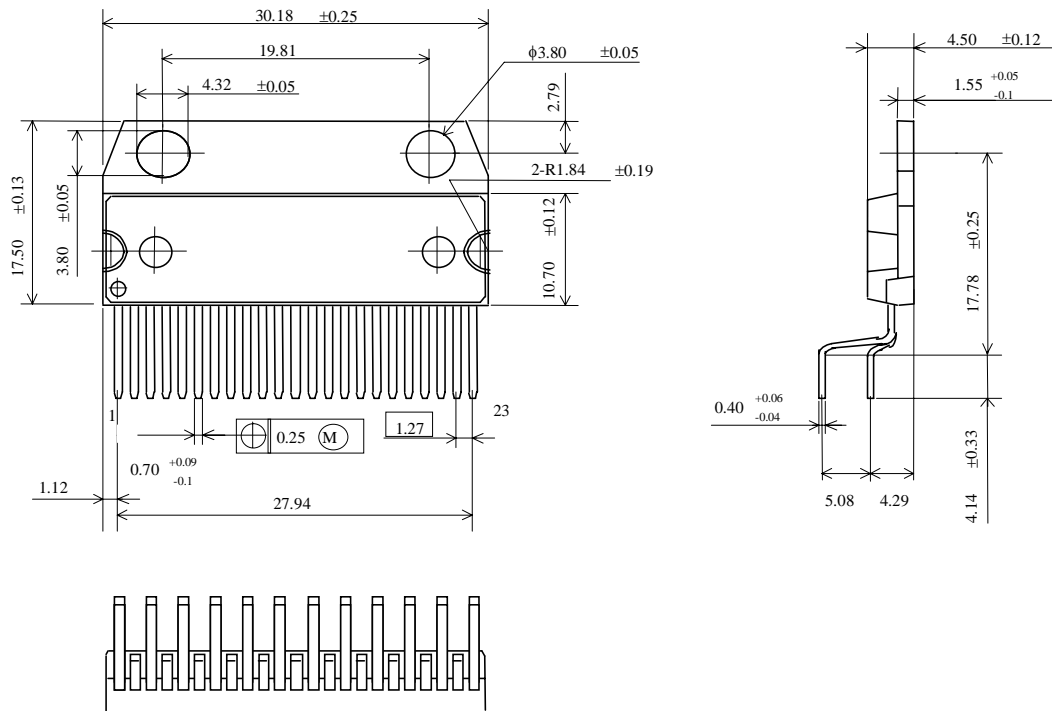


ECN3067SLR  
(SP-23TFA)

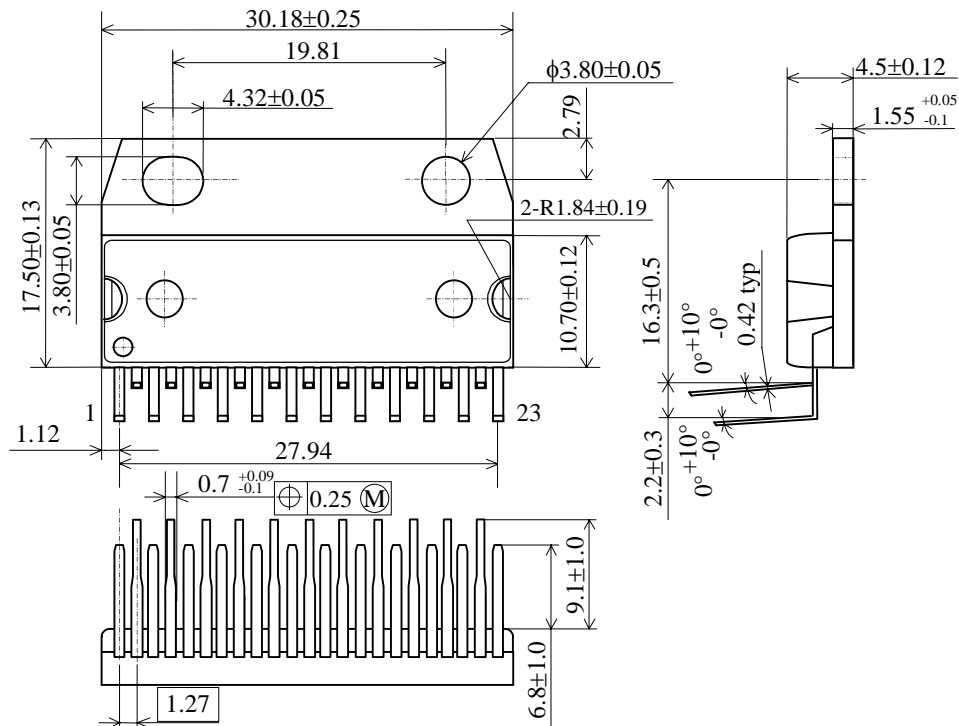
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## 9.Package Dimension ( unit: mm )

### (1) ECN3067SLV



### (2) ECN3067SLR





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## 10. Note of the design margin under the SOA

Following figure Indicates the evaluation as the reference of the SOA (safety operation area) under the  $T_j=135^{\circ}\text{C}$  ( the junction temperature is equal to  $135^{\circ}\text{C}$  ). Dot mark ( • ) shows the points of the IC destruction. The plural points under the same voltage Indicates the dispersion of the sample.

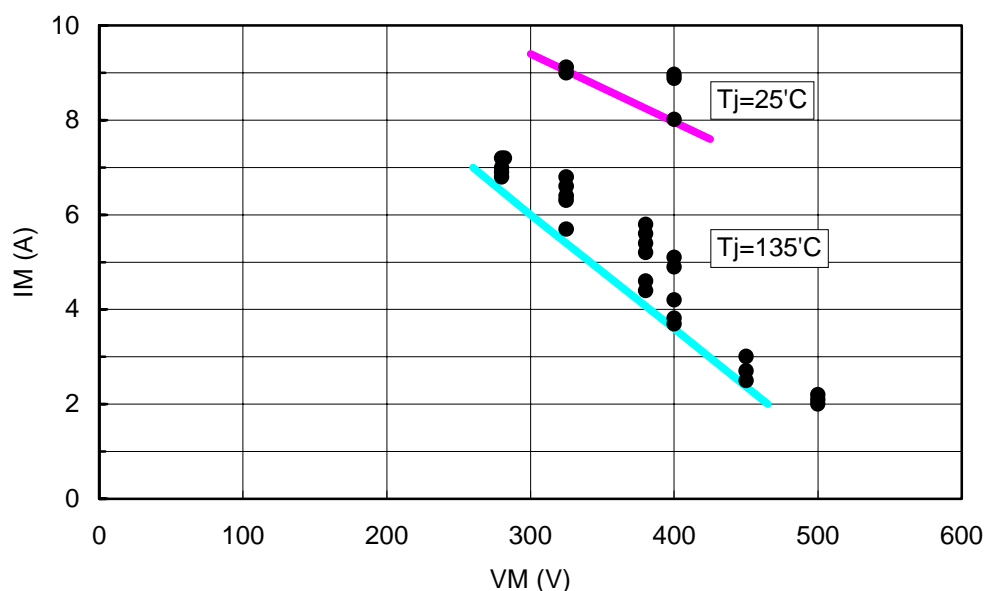


Fig. The Safety Operation Area in ECN3067 (reference)

In this figure, IM and VM are the current and the voltage at the terminal of motorwiring at the change of phase (turn on and turn off).

# HITACHI POWER SEMICONDUCTORS

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